



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20201202000.2

**Qualification of AIZU as an additional Fab Site option for select CMOS9T devices
Change Notification / Sample Request**

Date: December 07, 2020

To: TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If samples or additional data are required, requests must be received within **30 days** of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the PCN Team (PCN_ww_admin_team@list.ti.com). For sample requests or sample related questions, contact your local Field Sales Representative.

Sincerely,

PCN Team
SC Business Services

20201202000.2
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past sixty (60) months. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
LP5907QMFx-3.3Q1	null
LP5907QMFx-1.8Q1	null
LP5907QMFx-3.0Q1	null
LP5907QMFx-2.8Q1	null

Technical details of this Product Change follow on the next page(s).

PCN Number:	20201202000.2		PCN Date:	Dec 7, 2020																			
Title:	Qualification of AIZU as an additional Fab Site option for select CMOS9T devices																						
Customer Contact:	PCN Manager		Dept:	Quality Services																			
Proposed 1st Ship Date:	Jun 7, 2021		Estimated Sample Availability:	Date provided at sample request.																			
Change Type:																							
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Assembly Materials																		
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification																		
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process																		
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process																		
<input checked="" type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials	<input type="checkbox"/>	Wafer Fab Process																		
		<input type="checkbox"/>	Part number change																				
PCN Details																							
Description of Change:																							
Texas Instruments is pleased to announce the qualification of its AIZU fabrication facility as an additional Wafer Fab source for the selected devices listed in "Product Affected" section.																							
<table border="1" style="width: 100%;"> <thead> <tr> <th colspan="3">Current Sites</th> <th colspan="3">Additional Sites</th> </tr> <tr> <th>Current Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Additional Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>MAINEFAB</td> <td>CMOS9T</td> <td>200mm</td> <td>AIZU</td> <td>CMOS9T</td> <td>200mm</td> </tr> </tbody> </table>						Current Sites			Additional Sites			Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	MAINEFAB	CMOS9T	200mm	AIZU	CMOS9T	200mm
Current Sites			Additional Sites																				
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter																		
MAINEFAB	CMOS9T	200mm	AIZU	CMOS9T	200mm																		
Qual details are provided in the Qual Data Section.																							
Reason for Change:																							
Continuity of Supply																							
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																							
None																							
Changes to product identification resulting from this PCN:																							
Current																							
Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City																				
MAINEFAB	CUA	USA	South Portland																				
New Fab Site																							
Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City																				
AIZU	CU2	JPN	Aizuwakamatsu-shi																				
Sample product shipping label (not actual product label)																							
Product Affected:																							
LP5907QMFx-1.2Q1	LP5907QMFx-2.5Q1	LP5907QMFx-3.0Q1	LP5907QMFx-3.8Q1																				
LP5907QMFx-1.8Q1	LP5907QMFx-2.8Q1	LP5907QMFx-3.3Q1	LP5907QMFx-4.5Q1																				

Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)

Offload : LP5907AZ (CMOS9T) : Aizu Fab (From MFAB) DBV at TIEM Q100 Grade1

Approved
October 16, 2019

Product Attributes

Attributes	Qual Device: LP5907QMF-1.2Q1	Qual Device: LP5907QMF-1.8Q1	Qual Device: LP5907QMF-2.5Q1	Qual Device: LP5907QMF-2.8Q1	Qual Device: LP5907QMF-3.0Q1	Qual Device: LP5907QMF-3.3Q1	Qual Device: LP5907QMF-3.8Q1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Power Management	Power Management	Power Management	Power Management	Power Management	Power Management	Power Management
Die Attributes	-	-	-	-	-	-	-
Wafer Process ID	CMOS9T	CMOS9T	CMOS9T	CMOS9T	CMOS9T	CMOS9T	CMOS9T
Package Attributes	-	-	-	-	-	-	-
Assembly Site	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT	TIEM	TIEM
Package Type	SOT-23	SOT-23	SOT-23	SOT-23	SOT-23	SOT-23	SOT-23
Package Designator	DBV	DBV	DBV	DBV	DBV	DBV	DBV
Ball/Lead Count	5	5	5	5	5	5	5
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0

Product Attributes

Attributes	Qual Device: LP5907QMF-4.5Q1	QBS Process Reference: BQ76PL455APFC-Q1	QBS Process Reference: LDC1612QDNTQ1	QBS Process Reference: LDC1614QQRHRQ1	QBS Product/Process Reference LP5907xxQDQNRQ1	QBS Package Reference: LM4128AQ1MF-4.1	QBS Package Reference: LP5907QMF-4.5Q1
Automotive Grade Level	Grade 1	Grade 2	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +105 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Power Management	Power Management	Signal Chain	Signal Chain	Power Management	Power Management	Power Management
Die Attributes	-	-	-	-	-	-	-
Wafer Process ID	CMOS9T	CMOS9T, VIP50CLZ3	CMOS 9T	CMOS 9T	CMOS 9T	CMOS CS65	CMOS9T
Package Attributes	-	-	-	-	-	-	-
Assembly Site	TIEM	TITL (TAI)	TIEM	TIEM	Hana	TIEM	TIEM
Package Type	SOT-23	TQFP	WSON	WQFN	uQFN	SOT23	SOT-23
Package Designator	DBV	PFC	DNT	RGH	DQN	DBV	DBV
Ball/Lead Count	5	80	12	16	4	5	5
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0

- QBS: Qual By Similarity
- Qual Device LP5907QMF-3.8Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-1.2Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-2.8Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-3.0Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-3.3Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-4.5Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-1.8Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMF-2.5Q1 is qualified at LEVEL1-260C

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMFx -1.2Q1</u>	Qual Device: <u>LP5907QMFx -1.8Q1</u>	Qual Device: <u>LP5907QMFx -2.5Q1</u>	Qual Device: <u>LP5907QMFx -2.8Q1</u>	Qual Device: <u>LP5907QMFx -3.0Q1</u>	Qual Device: <u>LP5907QMFx -3.3Q1</u>	Qual Device: <u>LP5907QMFx -3.8Q1</u>
Test Group A – Accelerated Environment Stress Tests													
PTC	A 5	JEDEC JESD22 -A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	N/A	N/A	N/A	N/A	N/A	N/A
Test Group B – Accelerated Lifetime Simulation Tests													
Test Group C – Package Assembly Integrity Tests													
SBS	C 5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	N/A for Package	N/A for Package	N/A for Package	N/A for Package	N/A for Package	N/A for Package	N/A for Package
SBS	C 5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	N/A for Package	N/A for Package	N/A for Package	N/A for Package	N/A for Package	N/A for Package	N/A for Package
Test Group D – Die Fabrication Reliability Tests													
EM	D 1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD B	D 2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D 3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D 4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMFx -1.2Q1</u>	Qual Device: <u>LP5907QMFx -1.8Q1</u>	Qual Device: <u>LP5907QMFx -2.5Q1</u>	Qual Device: <u>LP5907QMFx -2.8Q1</u>	Qual Device: <u>LP5907QMFx -3.0Q1</u>	Qual Device: <u>LP5907QMFx -3.3Q1</u>	Qual Device: <u>LP5907QMFx -3.8Q1</u>
SM	D 5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E – Electrical Verification Tests													
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	1000 V	1/3/0	-	-	-	-	1/3/0	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	1500 V	1/3/0	-	-	-	-	1/3/0	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	2000 V	1/3/0	-	-	-	-	1/3/0	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	2500 V	1/3/0	-	-	-	-	1/3/0	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	3000 V	1/3/0	-	-	-	-	1/3/0	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	4000 V	1/3/0	-	-	-	-	1/3/0	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	500 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	1000 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	250 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	500 V	1/3/0	-	-	-	-	1/3/0	-

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LP5907QMF X-1.2Q1	Qual Device: LP5907QMF X-1.8Q1	Qual Device: LP5907QMF X-2.5Q1	Qual Device: LP5907QMF X-2.8Q1	Qual Device: LP5907QMF X-3.0Q1	Qual Device: LP5907QMF X-3.3Q1	Qual Device: LP5907QMF X-3.8Q1
		011											
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	750 V	1/3/0	-	-	-	-	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-up	Latchup/125c	1/6/0	-	-	-	-	-	-
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LP5907QMF X-4.5Q1	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	QBS Product/Process Reference: LP5907xxQDQN RQ1	QBS Package Reference: LM4128AQ1 MF-4.1	QBS Package Reference: LP5907QMF X-4.5Q1
Test Group A – Accelerated Environment Stress Tests													
PC	A1	JEDEC J-STD-020 JESD2 2-A113	3	77	Automotive Preconditioning Level 1	3X IR REFLOW/260 C+5 / -0C	1/160/0	-	-	3/693/0		3/893/0	1/392/0
PC	A1	JEDEC J-STD-020 JESD2 2-A113	3	77	Automotive Preconditioning Level 3	Auto Precon L3/260	-	1/270/0	4/770/0	-		-	-
HAST	A2	JEDEC JESD2 2-A110	3	77	Biased HAST, 110C/85%RH	264 hours	-	1/77/0	-	-		-	-
HAST	A2	JEDEC JESD2 2-A110	3	77	Biased HAST, 130C/85%RH	96HRS	1/77/0	-	3/231/0	3/231/0		3/231/0	1/160/0
AC	A3	JEDEC JESD2 2-A102	3	77	Autoclave 121C	96HRS	1/77/0	1/77/0	3/231/0	3/231/0		3/231/0	1/77/0
TC	A4	JEDEC JESD2 2-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500CYC	1/77/0	1/77/0	3/231/0	3/231/0		3/231/0	1/77/0
TC-WBP	A4	MIL-STD883 Method 2011	1	30	Auto Post TC Bond Pull	per MIL-STD 883 Method 2011	1/30/0	1/30/0	1/30/0	1/30/0		1/Pass	1/30/0
PTC	A5	JEDEC JESD2	1	45	Power Temperature	1000 Cycles	N/A	-	-	-		-	-

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMF</u> <u>X-4.5Q1</u>	QBS Process Reference: <u>BQ76PL455AP</u> <u>FC-Q1</u>	QBS Process Reference: <u>LDC1612QDN</u> <u>TQ1</u>	QBS Process Reference: <u>LDC1614QRGH</u> <u>RQ1</u>	QBS Product/Process Reference LP5907xxQDQN RQ1	QBS Package Reference: <u>LM4128AQ1</u> <u>MF-4.1</u>	QBS Package Reference: : <u>LP5907QM</u> <u>FX-4.5Q1</u>
		2-A106			Cycle								
HTS L	A 6	JEDEC JESD2 2-A103	1	45	High Temp Storage Bake 150C	1000 hours	1/77/0	-	1/77/0	1/45/0		-	-
HTS L	A 6	JEDEC JESD2 2-A103	1	45	High Temp Storage Bake 175C	500 hours	-	-	-	-		-	3/231/0
Test Group B – Accelerated Lifetime Simulation Tests													
HTO L	B 1	JEDEC JESD2 2-A108	3	77	Life Test, 125C	1000HRS	1/77/0	3/231/0	3/230/0	1/77/0	2/154/0	3/231/0	2/154/0
ELF R	B 2	AEC Q100-008	3	800	Auto Early Life Failure Rate Grade 1	150C(24 Hrs)	-	-	-	-		3/2400/0	-
ELF R	B 2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	125C (24 Hrs).	-	3/2400/0	-	-		-	-
ELF R	B 2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 hours	-	-	3/2400/0	-		-	2/800/0
EDR	B 3	AEC Q100-005	3	77	NVM Endurance, Data Retention,	-	N/A	-	-	-		-	-
EDR	B 3	AEC Q100-005	3	77	W/E Endur High Temp	W/E 100cy/125C + 150C/1000hrs.	-	3/231/0	-	-		-	-
EDR	B 3	AEC Q100-005	3	77	W/E Endur Low Temp	W/E 100cy/ -40C + 150C/1000hrs.	-	3/231/0	-	-		-	-
EDR	B 3	AEC Q100-005	3	77	W/E Endur Room Temp	W/E 100cy/25C + 150C/1000hrs.	-	3/231/0	-	-		-	-
Test Group C – Package Assembly Integrity Tests													
WB S	C 1	AEC Q100-001	1	30	Auto Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk > 1.67	3/90/0	1/30/0	-	-		-	-
WB P	C 2	MIL-STD88	1	30	Bond Pull	30 Wire, 5 units min	3/90/0	1/30/0	-	-		1/Pass	-

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LP5907QMF X-4.5Q1	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	QBS Product/Process Reference: LP5907xxQDQN RQ1	QBS Package Reference: LM4128AQ1 MF-4.1	QBS Package Reference: LP5907QM FX-4.5Q1
		3 Method 2011											
SD	C 3	JEDEC JESD2 2-B102	1	15	Solderability	Steam age, 8 hours; PB-Free solder	1/15/0	-	-	1/30/0	-	1/Pass	-
PD	C 4	JEDEC JESD2 2-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	3/30/0	-	3/Pass	3/30/0		1/Pass	-
SBS	C 5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	N/A for Package	-	-	-		-	-
SBS	C 5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	N/A for Package	-	-	-		-	-
LI	C 6	JEDEC JESD2 2-B105	1	50	Lead Pull to Destruction	To Dest./Rec.Data	-	1/50/0	-	-		-	-
Test Group D – Die Fabrication Reliability Tests													
EM	D 1	JESD6 1	-	-	Electromigration	-	Completed Per Process Technology Requirements	-	-	-		-	-
TDD B	D 2	JESD3 5	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-	-	-		-	-

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LP5907QMF X-4.5Q1	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	QBS Product/Process Reference: LP5907xxQDQN RQ1	QBS Package Reference: LM4128AQ1 MF-4.1	QBS Package Reference: LP5907QM FX-4.5Q1
HCI	D 3	JESD6 0 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-	-	-		-	-
NBT I	D 4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-	-	-		-	-
SM	D 5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-	-	-		-	-
Test Group E – Electrical Verification Tests													
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	500 V	1/3/0	-	-	-		1/3/0	1/3/0
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	1000 V	1/3/0	-	-	-		1/3/0	1/3/0
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	1500 V	1/3/0	-	-	-		1/3/0	1/3/0
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	2000 V	1/3/0	-	-	-		1/3/0	1/3/0
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	2500 V	1/3/0	-	3/9/0	1/3/0		1/3/0	1/3/0
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	3000 V	1/3/0	1/3/0	-	-		-	-
HBM	E 2	AEC Q100-002	1	3	ESD - HBM - Q100	4000 V	1/3/0	-	-	-		-	-

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMF</u> <u>X-4.5Q1</u>	QBS Process Reference: <u>BQ76PL455AP</u> <u>FC-Q1</u>	QBS Process Reference: <u>LDC1612QDN</u> <u>TQ1</u>	QBS Process Reference: <u>LDC1614QRGH</u> <u>RQ1</u>	QBS Product/Process Reference <u>LP5907xxQDQN</u> <u>RQ1</u>	QBS Package Reference: <u>LM4128AQ1</u> <u>MF-4.1</u>	QBS Package Reference: : <u>LP5907QM</u> <u>FX-4.5Q1</u>
CD M	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	1000 V	1/3/0	-	3/9/0	1/3/0		1/3/0	1/3/0
CD M	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	1/3/0	-	-	-		-	1/3/0
CD M	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	250 V	1/3/0	-	-	-		-	1/3/0
CD M	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	500 V	1/3/0	-	-	-		1/3/0	1/3/0
CD M	E 3	AEC Q100-011	1	3	ESD - CDM - Q100	750 V	1/3/0	1/3/0	-	-		1/3/0	1/3/0
LU	E 4	AEC Q100-004	1	6	Latch-up	25C	1/6/0	1/6/0	3/18/0	1/6/0		1/6/0	1/6/0
LU	E 4	AEC Q100-004	1	6	Latch-up	Latchup/125c	1/6/0	1/6/0	3/18/0	1/6/0		1/6/0	1/6/0
ED	E 5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0	3/Pass	3/Pass	3/Pass		1/Pass	-
Additional Tests													
-			-	-	Auto Solderability (Pb)	>95% Lead Coverage 8 Hr Steam Age	-	-	1/Pass	-		-	-
-			-	-	Auto Solderability (Pb-Free)	>95% Lead Coverage 8 Hr Steam Age	-	-	1/Pass	-		-	-
-			-	-	Precondition Prior to HTSL	3X IR REFLOW/260 C+5 / -0C	1/80/0	-	-	-		-	-
MQ			-	-	Manufacturability (Auto Assembly)	(per automotive requirements)	3/Pass	1/Pass	3/Pass	3/Pass		1/Pass	-
MQ			-	-	Manufacturability (Wafer Fab)	(per mfg. Site specification)		1/Pass	3/Pass	-		-	-

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C

Grade 3 (or L): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB/HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
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